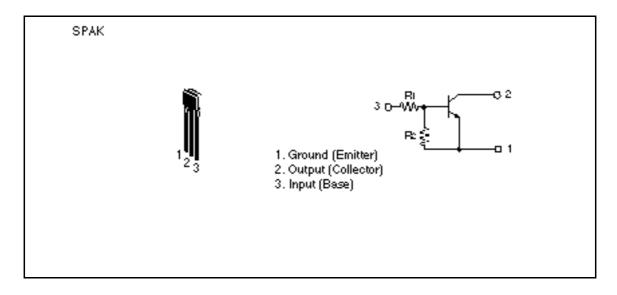
Silicon NPN with Internal Resistance

HITACHI

Application

Low frequency amplifier, Muting, Switching, Inverter

Outline



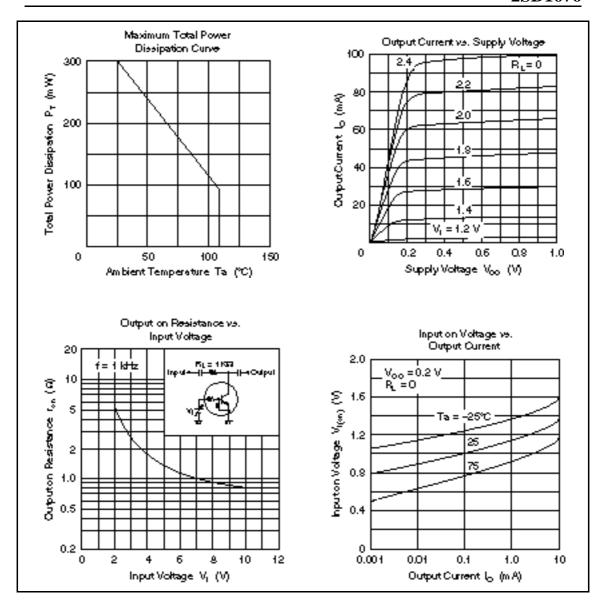


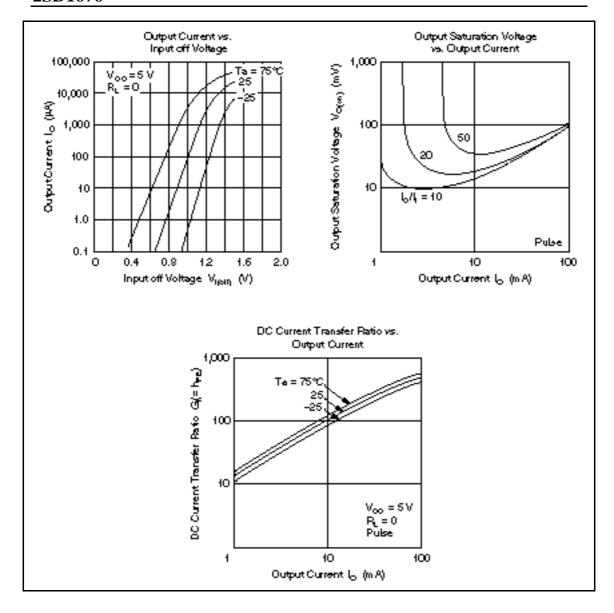
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit
Supply voltage	V _{cc}	20	V
Input voltage	V _I	±10	V
Output current	Io	600	mA
Total power dissipation	P _T	300	mW
Operating temperature	T_OP	-25 to +110	°C
Storage temperature	Tstg	-55 to +150	°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Input on voltage	$V_{I(on)}$	1.1	_	1.7	V	$V_{CC} = 0.2 \text{ V}, I_{O} = 10 \text{ mA}$
Input off voltage	$V_{I(off)}$	0.5		1.2	V	$V_{CC} = 5 \text{ V}, I_{O} = 10 \mu\text{A}$
Output saturation voltage	$V_{O(on)}$	_	20	40	mV	$I_0 = 10 \text{ mA}, I_1 = 0.5 \text{ mA}$
Output cutoff current	I _{O(off)}	_	_	0.5	μA	$V_{cc} = 5 \text{ V}, V_{i} = 0$
DC current transfer ratio	Gi	60	100	_		$V_{cc} = 5 \text{ V}, I_{o} = 10 \text{ mA}$
Input resistance	R ₁	_	6.8	_	k	
Resistance ratio	R_1/R_2	0.9	1.0	1.1		
Turn on time	t _{on}	_	0.3	_	μS	$V_{CC} = 5 \text{ V}, V_I = 5 \text{ V}, R_L = 1 \text{k}$
Storage time	t _{stg}	_	1.5	_	μS	_
Fall time	t _f	_	0.7	_	μS	_
Output on resistance	r _{on}		1.0	_		$V_1 = 7 \text{ V}, R_L = 1 \text{k}, f = 1 \text{kHz}$





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